

61058

**SILICON PHOTOTRANSISTOR
(TYPE GS4021)**

Mii
OPTOELECTRONIC PRODUCTS
DIVISION

Features:

- Hermetically sealed
- High sensitivity
- Base lead provided for conventional transistor biasing
- Narrow viewing angle
- Spectrally matched to the 62033 series LED.

Applications:

- Incremental encoding
- Reflective sensors
- Position sensors
- Level sensors

DESCRIPTION

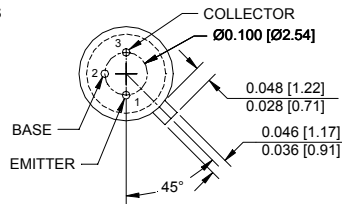
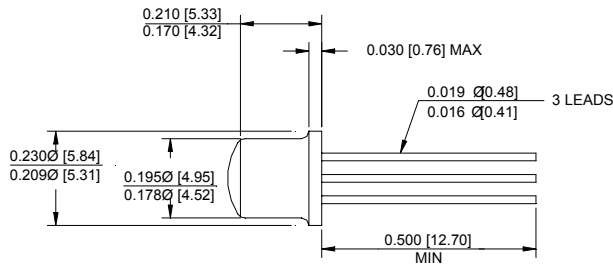
The **61058** is an N-P-N Planar Silicon phototransistor in a lensed TO-46 three-lead package. It is available in a range of sensitivities and is ideal for use wherever high response, low dark current leakage, and low saturation characteristics are required. Available custom binned to customer specifications or screened to MIL-PRF-19500.

ABSOLUTE MAXIMUM RATINGS

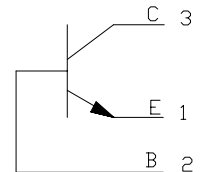
Storage Temperature.....	-65°C to +150°C
Operating Temperature (See part selection guide for actual operating temperature)	-65°C to +125°C
Collector-Emitter Voltage.....	50V
Emitter-Collector Voltage.....	7V
Continuous Collector Current	50mA
Power Dissipation (Derate at the rate of 2.5 mW/°C above 25°C)	250mW
Lead Soldering Temperature (1/16" from case for 10 seconds).....	240°C

Package Dimensions

Schematic Diagram



THE COLLECTOR IS IN ELECTRICAL CONTACT WITH THE CASE



ALL DIMENSIONS ARE IN INCHES [MILLIMETERS]

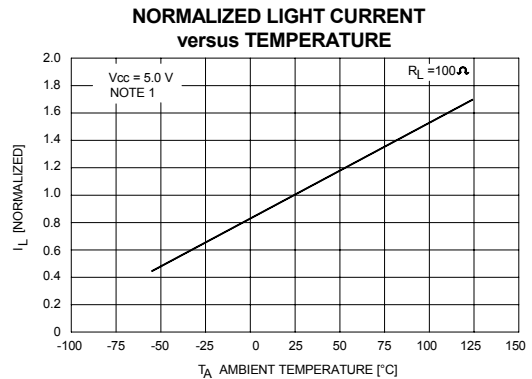
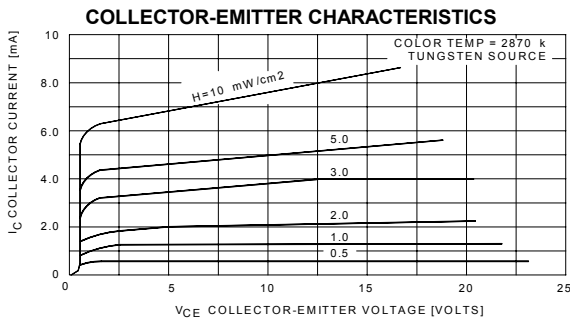
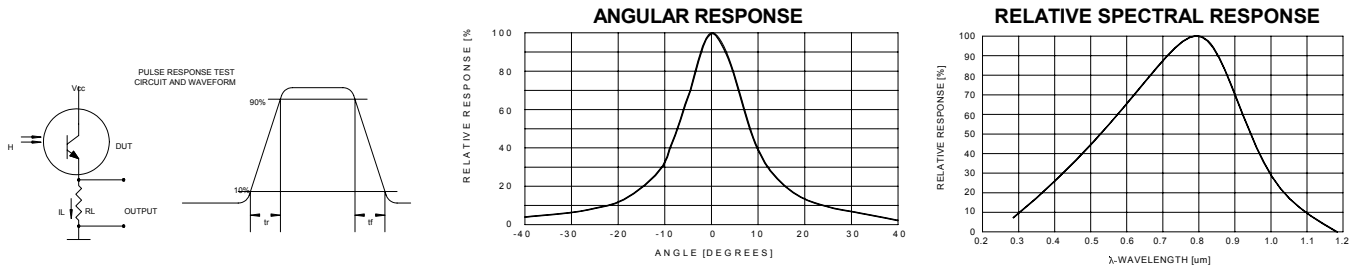
ELECTRICAL CHARACTERISTICS

T_A = 25°C unless otherwise specified.

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS	NOTE
Light Current	61058-X01 61058-X02 61058-X03 61058-X04	1 4 8 15		5 9 16 --	mA	V _{CE} = 5.0V, H = 5 mW/cm ²	1
Dark Current	61058-XXX			100	nA	V _{CE} = 10V, H = 0	
Collector-Emitter Breakdown Voltage	61058-XXX	30			V	I _C = 100µA	
Emitter-Collector Breakdown Voltage	61058-XXX	7			V	I _E = 100µA	
Light Current Rise Time	61058-X01 61058-X02 61058-X03 61058-X04		3.0 4.0 5.0 7.0		µs	R _L = 1KΩ, V _{CC} = 5V, I _L = 1.0mA	
Saturation Voltage	61058-XXX		0.2		V	I _C = 0.4mA, H = 5 mW/cm ²	
Angular Response	61058-XXX		10		degrees		2

NOTES:

1. Irradiance in mW/cm² from a tungsten source at a color temperature of 2870K..
2. The angle between incidence for peak response and incidence for 50% of peak response.



RECOMMENDED OPERATING CONDITIONS:

PARAMETER	SYMBOL	MIN	MAX	UNITS
Bias Voltage-Collector/Emitter	V _F	5	10	mA
Irradiance (H)	H	15	25	mW/cm ²

SELECTION GUIDE

PART NUMBER	PART DESCRIPTION	I _L Range
61058-001	Silicon Phototransistor in TO-46 package, commercial version	1 to 5mA
61058-101	Silicon Phototransistor in TO-46 package (-55° to +125°C) with 100% screening	1 to 5mA
61058-002	Silicon Phototransistor in TO-46 package, commercial version	4 to 9mA
61058-102	Silicon Phototransistor in TO-46 package (-55° to +125°C) with 100% screening	4 to 9mA
61058-003	Silicon Phototransistor in TO-46 package, commercial version	8 to 16mA
61058-103	Silicon Phototransistor in TO-46 package (-55° to +125°C) with 100% screening	8 to 16mA
61058-004	Silicon Phototransistor in TO-46 package, commercial version	15+ mA
61058-104	Silicon Phototransistor in TO-46 package (-55° to +125°C) with 100% screening	15+ mA